



C945 TRANSISTOR (NPN)

TO-92

FEATURE

- ⊗ Excellent h_{FE} linearity
- ⊗ Low noise
- ⊗ Complementary to A733

- 1.EMITTER
- 2.COLLECTOR
- 3. BASE

MAXIMUM RATINGS (T=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	60	V
V_{CE0}	Collector-Emitter Voltage	50	V
V_{EB0}	Emitter-Base Voltage	5	V
I_c	Collector Current -Continuous	150	mA
P_c	Collector Power Dissipation	400	mW
T_J	Junction Temperature	125	°C
T_{stg}	Storage Temperature	-55-125	°C



ELECTRICAL CHARACTERISTICS (T=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_c=1mA, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_c=100\mu A, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=100\mu A, I_c=0$	5			V
Collector cut-off current	I_{CB0}	$V_{CB}=60V, I_E=0$			0.1	μA
Collector cut-off current	I_{CE0}	$V_{CE}=45V, I_B=0$			0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB}=5V, I_c=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6V, I_c=1mA$	70		700	
	$h_{FE(2)}$	$V_{CE}=6V, I_c=0.1mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=100mA, I_B=10mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c=100mA, I_B=10mA$			1	V
Transition frequency	f_T	$V_{CE}=6V, I_c=10mA, f=30MHz$	200			MHz
Collector output capacitance	C	$V_{CB}=10V, I_E=0, f=1MHz$			3.0	pF
Noise figure	NF^{ob}	$V_{CE}=6V, I_c=0.1mA$ $R_G=10k\Omega, f=1MHz$			10	dB

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700

Typical Characteristics

